

MOSFETs Silicon P-Channel MOS (U-MOSVI)

TPCC8107

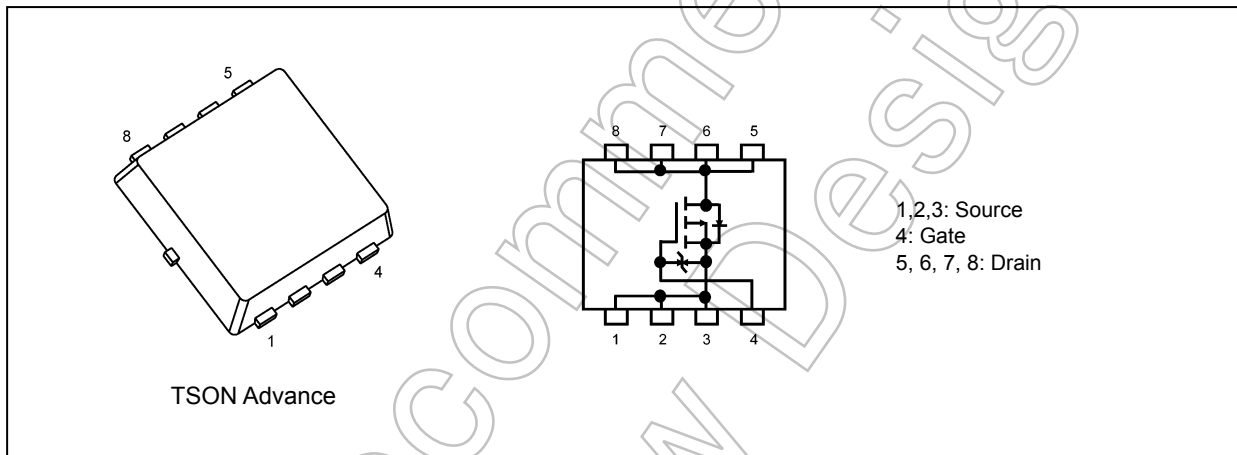
1. Applications

- Motor Drivers
- DC-DC Converters
- Switching Voltage Regulators

2. Features

- (1) Small, thin package
- (2) Low drain-source on-resistance: $R_{DS(ON)} = 23.5 \text{ m}\Omega$ (typ.) ($V_{GS} = -10 \text{ V}$)
- (3) Low leakage current: $I_{DSS} = -10 \text{ }\mu\text{A}$ (max) ($V_{DS} = -60 \text{ V}$)
- (4) Enhancement mode: $V_{th} = -2.0$ to -3.0 V ($V_{DS} = -10 \text{ V}$, $I_D = -1.0 \text{ mA}$)

3. Packaging and Internal Circuit



Start of commercial production
2012-07

4. Absolute Maximum Ratings (Note) ($T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V_{DSS}	-60	V
Gate-source voltage	V_{GSS}	-20/+10	
Drain current (DC) (Note 1)	I_D	-25	A
Drain current (pulsed) (Note 1)	I_{DP}	-75	
Power dissipation ($T_c = 25^\circ\text{C}$)	P_D	46.8	W
Power dissipation ($t = 10$ s) (Note 2)	P_D	2.27	W
Power dissipation ($t = 10$ s) (Note 3)	P_D	0.84	W
Single-pulse avalanche energy (Note 4)	E_{AS}	63.0	mJ
Avalanche current	I_{AR}	-25	A
Channel temperature (Note 5)	T_{ch}	175	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance ($T_c = 25^\circ\text{C}$)	$R_{th(ch-c)}$	3.2	$^\circ\text{C/W}$
Channel-to-ambient thermal resistance ($t = 10$ s) (Note 2)	$R_{th(ch-a)}$	66	$^\circ\text{C/W}$
Channel-to-ambient thermal resistance ($t = 10$ s) (Note 3)	$R_{th(ch-a)}$	178	$^\circ\text{C/W}$

Note 1: Ensure that the channel temperature does not exceed 175°C .

Note 2: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 3: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 4: $V_{DD} = -25$ V, $T_{ch} = 25^\circ\text{C}$ (initial), $L = 137$ μH , $R_G = 25$ Ω , $I_{AR} = -25$ A

Note 5: Merely channel temperature is guaranteed 175°C .

Storage temperature range is guaranteed as usual (-55 to 150°C).

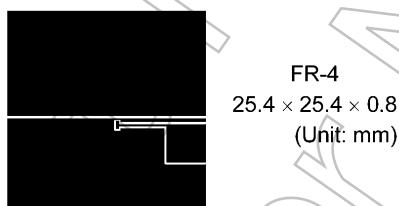


Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)

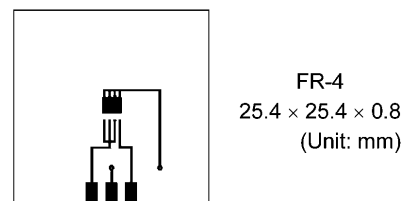


Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

6.1. Static Characteristics ($T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	I_{GSS}	$V_{GS} = -16/+10\text{ V}, V_{DS} = 0\text{ V}$	—	—	± 10	μA
Drain cut-off current	I_{DSS}	$V_{DS} = -60\text{ V}, V_{GS} = 0\text{ V}$	—	—	-10	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = -10\text{ mA}, V_{GS} = 0\text{ V}$	-60	—	—	V
Drain-source breakdown voltage (Note 6)	$V_{(BR)DSX}$	$I_D = -10\text{ mA}, V_{GS} = 10\text{ V}$	-50	—	—	
Gate threshold voltage	V_{th}	$V_{DS} = -10\text{ V}, I_D = -1.0\text{ mA}$	-2.0	—	-3.0	
Drain-source on-resistance	$R_{DS(ON)}$	$V_{GS} = -6\text{ V}, I_D = -12.5\text{ A}$	—	26.8	42.9	$\text{m}\Omega$
		$V_{GS} = -10\text{ V}, I_D = -12.5\text{ A}$	—	23.5	30.5	

Note 6: If a reverse bias is applied between gate and source, this device enters $V_{(BR)DSX}$ mode. Note that the drain-source breakdown voltage is lowered in this mode.

6.2. Dynamic Characteristics ($T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Input capacitance	C_{iss}	$V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	2930	—	pF
Reverse transfer capacitance	C_{rss}		—	230	—	
Output capacitance	C_{oss}		—	270	—	
Switching time (rise time)	t_r	See Figure 6.2.1.	—	6	—	ns
Switching time (turn-on time)	t_{on}		—	15	—	
Switching time (fall time)	t_f		—	44	—	
Switching time (turn-off time)	t_{off}		—	206	—	

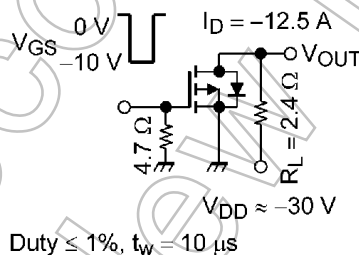


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Q_g	$V_{DD} \approx -48\text{ V}, V_{GS} = -10\text{ V}, I_D = -25\text{ A}$	—	63	—	nC
Gate-source charge 1	Q_{gs1}		—	9	—	
Gate-drain charge	Q_{gd}		—	18	—	

6.4. Source-Drain Characteristics ($T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Reverse drain current (pulsed) (Note 7)	I_{DRP}	—	—	—	-75	A
Diode forward voltage	V_{DSF}	$I_{DR} = -25\text{ A}, V_{GS} = 0\text{ V}$	—	—	1.2	V

Note 7: Ensure that the channel temperature does not exceed 175°C .

7. Marking

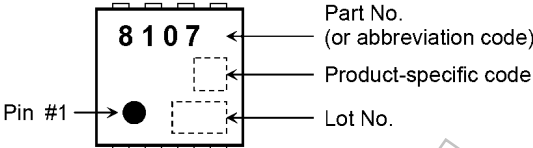


Fig. 7.1 Marking

Not Recommended for New Design

8. Characteristics Curves (Note)

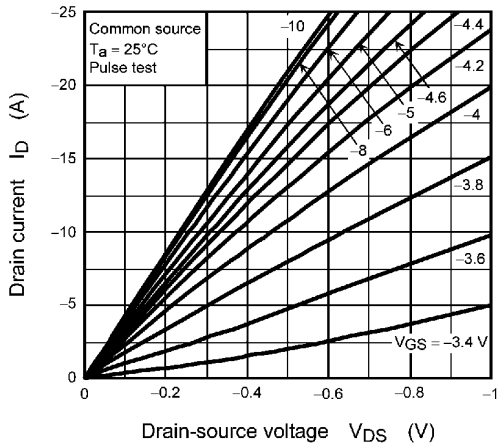


Fig. 8.1 $I_D - V_{DS}$

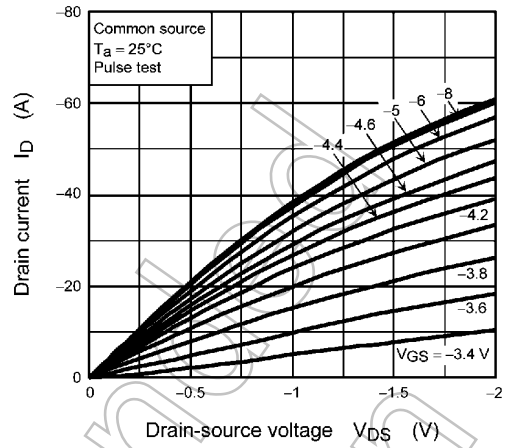


Fig. 8.2 $I_D - V_{DS}$

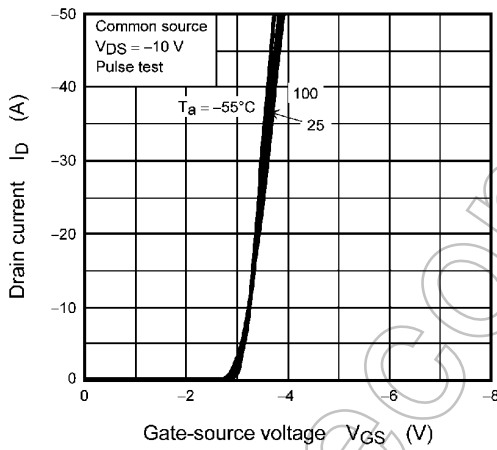


Fig. 8.3 $I_D - V_{GS}$

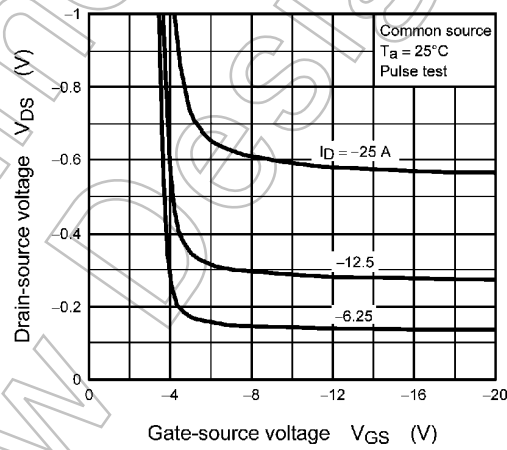


Fig. 8.4 $V_{DS} - V_{GS}$

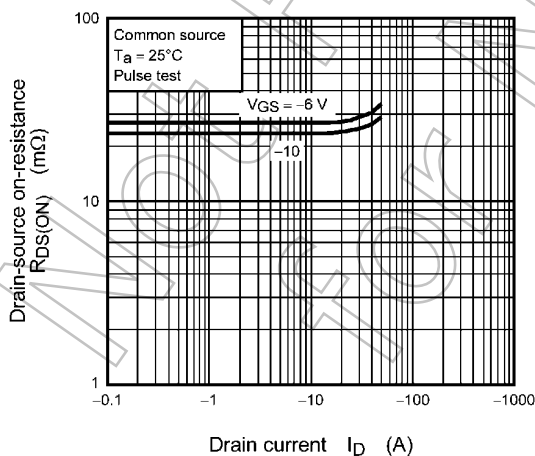


Fig. 8.5 $R_{DS(ON)} - I_D$

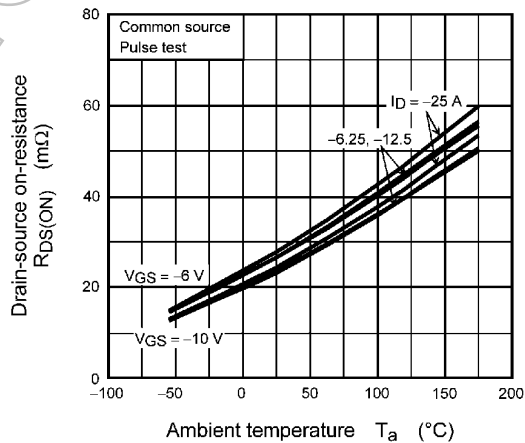


Fig. 8.6 $R_{DS(ON)} - T_a$ (Note 8)

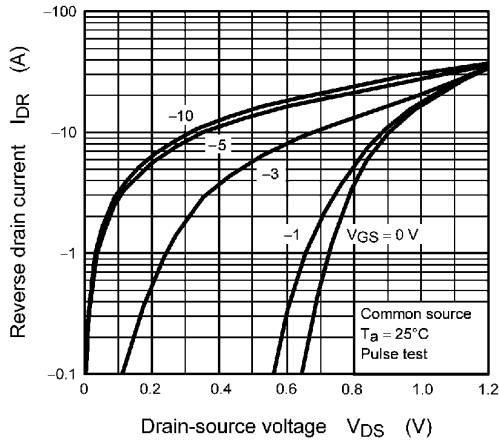


Fig. 8.7 $I_{DR} - V_{DS}$

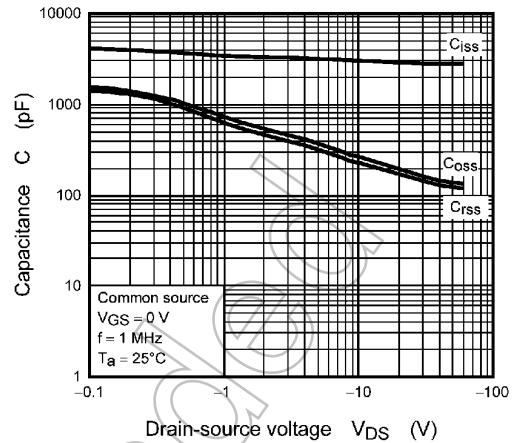


Fig. 8.8 Capacitance - V_{DS}

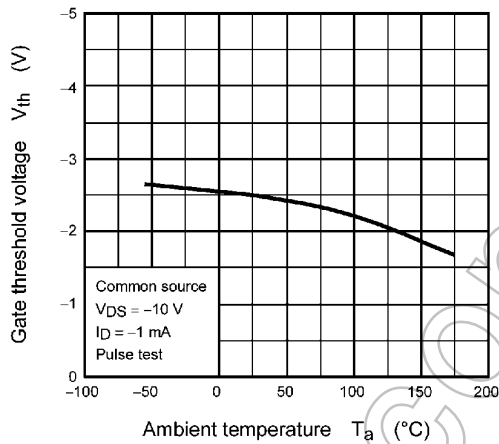


Fig. 8.9 $V_{th} - T_a$ (Note 8)

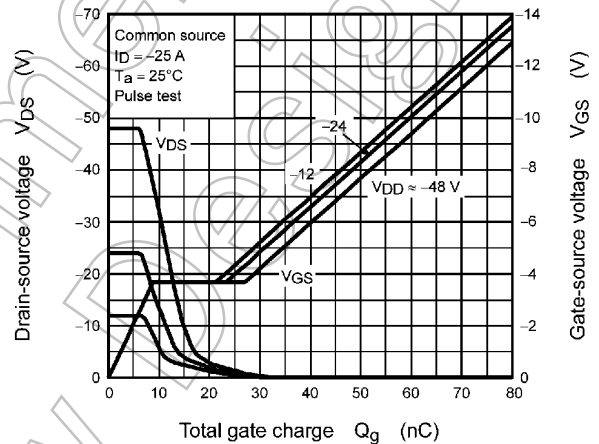


Fig. 8.10 Dynamic Input/Output Characteristics

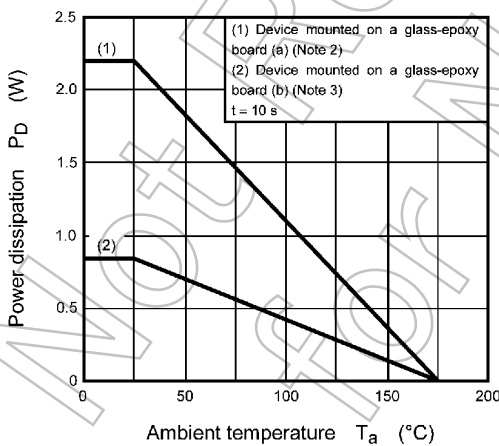


Fig. 8.11 $P_D - T_a$ (Note 8)
(Guaranteed Maximum)

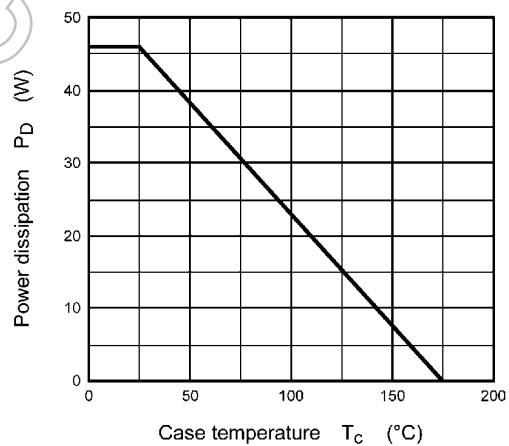


Fig. 8.12 $P_D - T_c$ (Note 8)
(Guaranteed Maximum)

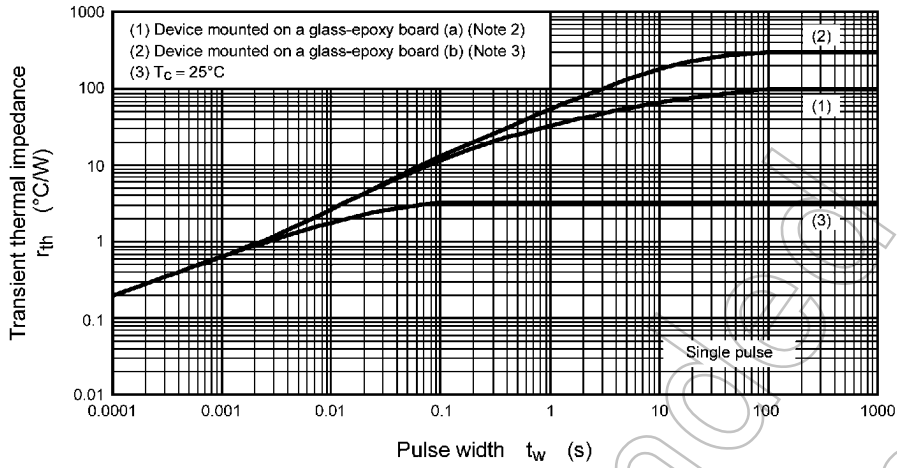


Fig. 8.13 $r_{th} - t_w$
(Guaranteed Maximum)

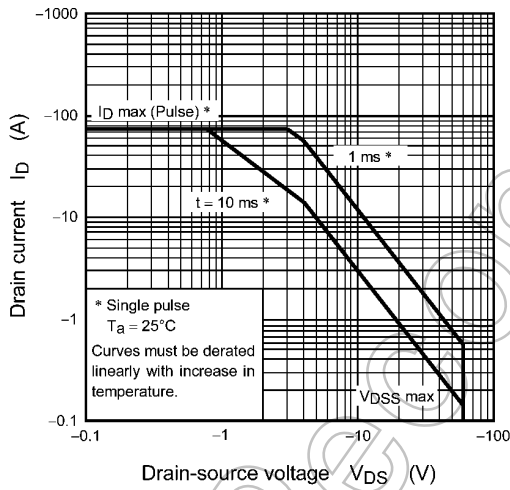


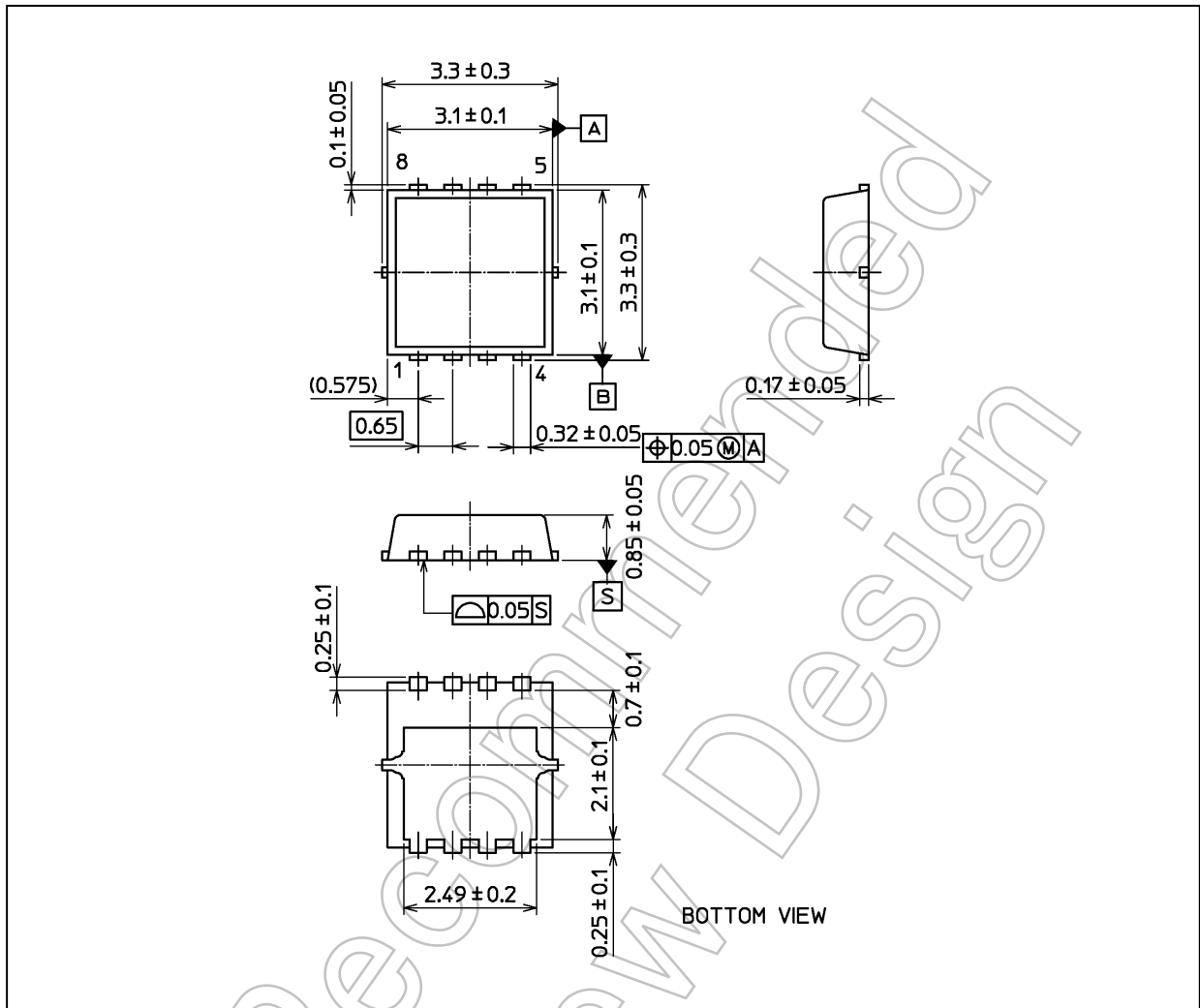
Fig. 8.14 Safe Operating Area
(Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Note 8: Although several performance curves are shown up to a T_a or T_c of 175°C , the device is not guaranteed at storage temperatures up to 175°C . The storage temperature (T_{stg}) range is rated at -55°C to 150°C .

Package Dimensions

Unit: mm



Weight: 0.02 g (typ.)

Package Name(s)
TOSHIBA: 2-3X1S
Nickname: TSON Advance

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